Zibo Seno Electronic Engineering Co., Ltd.









3.0A SURFACE MOUNT FAST RECOVERY DIODE

Features

- Ideally Suited for Automatic Assembly
- Low Forward Voltage Drop, High Efficiency
- Surge Overload Rating to 100A Peak
- Low Power Loss
- Ultra-Fast Recovery Time
- Plastic Case Material has UL Flammability Classification Rating 94V-O

A C + D + D + G + H + F G + E + D

	SI	ИΒ	SMC				
Dim	Min	Max	Min	Max			
Α	3.30	3.94	5.59	6.22			
В	4.06	4.57	6.60	7.11			
С	1.96	2.21	2.75	3.18			
D	0.15	0.31	0.15	0.31			
Ε	5.00	5.59	7.75	8.13			
G	0.10	0.20	0.10	0.20			
Н	0.76	1.52	0.76	1.52			
J	2.00	2.62	2.00	2.62			
	All Dim	ensions	in mm	•			

Mechanical Data

Case: SMC/DO-214AB, Molded Plastic

 Terminals: Solder Plated, Solderable per MIL-STD-750, Method 2026

- Polarity: Cathode Band or Cathode Notch
- Marking: Type Number
- Weight: SMB Weight: 0.093 grams (approx.)
 SMC Weight: 0.20 grams (approx.)
- Lead Free: For RoHS / Lead Free Version

Maximum Ratings and Electrical Characteristics @TA=25°C unless otherwise specified

Characteristic	Symbol	RS3A	RS3B	RS3D	RS3G	RS3J	RS3K	RS3M	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	VRRM VRWM VR	50	100	200	400	600	800	1000	٧
RMS Reverse Voltage	VR(RMS)	35	70	140	280	420	560	800	٧
Average Rectified Output Current @T_ = 100°C	lo	3.0						Α	
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	lFSM	100						Α	
Forward Voltage @I _F = 3.0A	VFM	1.3						V	
Peak Reverse Current $@T_A = 25^{\circ}C$ At Rated DC Blocking Voltage $@T_A = 100^{\circ}C$	IRM	10 500						μA	
Reverse Recovery Time (Note 1)	trr	150			250	250 500		nS	
Typical Junction Capacitance (Note 2)	Cj	50						pF	
Typical Thermal Resistance (Note 3)	R⊕JL	30						°C/W	
Operating and Storage Temperature Range	Tj, Tstg	-65 to +150						°C	

Note: 1. Measured with $\rm I_F$ = 0.5A, $\rm I_R$ = 1.0A, $\rm I_m$ = 0.25A. See figure 5.

- 2. Measured at 1.0 MHz and applied reverse voltage of 4.0 V DC.
- 3. Mounted on P.C. Board with 8.0mm² land area.

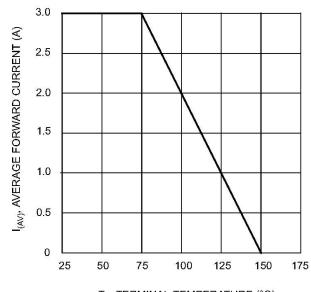
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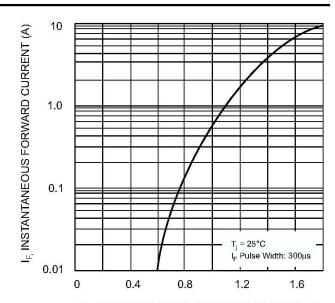
RS3A - RS3M







T_T, TERMINAL TEMPERATURE (°C) Fig. 1 Forward Current Derating Curve



V_F, INSTANTANEOUS FORWARD VOLTAGE (V) Fig. 2 Typical Forward Characteristics

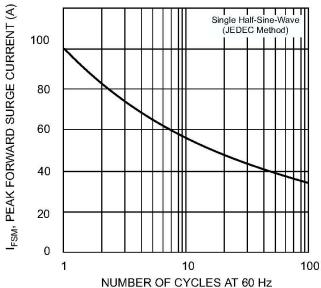


Fig. 3 Forward Surge Current Derating Curve

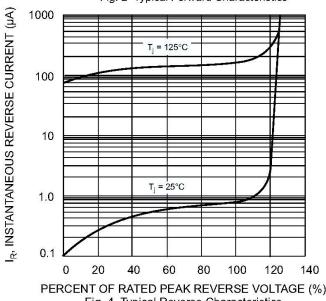
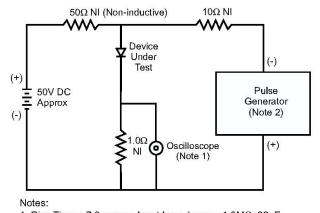


Fig. 4 Typical Reverse Characteristics



1. Rise Time = 7.0ns max. Input Impedance = 1.0MΩ, 22pF.

2. Rise Time = 10ns max. Input Impedance = 50Ω .

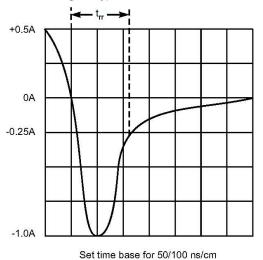


Fig. 5 Reverse Recovery Time Characteristic and Test Circuit